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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:	)	Group Art Unit: 2812
KUWAZAWA	)	
Serial No. 09 885,761	)	Examiner: Isaac, Stanetta D.
Filed: June 19, 2001	)	
For: METHODS FOR MANUFACTURING	)	
SEMICONDUCTOR DEVICES AND	)	
SEMICONDUCTOR DEVICES	)	

AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sirs:

In response to the Office Action dated May 20, 2002, please enter and consider the following:

IN THE DRAWINGS:

In Figs. 5-6, applicant proposes to insert the terms --Prior Art--.

IN THE CLAIMS:

Please cancel claims 10-20 without prejudice.

Please amend claims 1-3 and 21-24 as follows:

1. (amended) A method for manufacturing a semiconductor device, the method comprising:
- (a) forming a gate dielectric layer over a semiconductor substrate;
  - (b) forming a gate electrode over the gate dielectric layer;
  - (c) forming a dielectric layer over the semiconductor substrate;
  - (d) forming a mask layer over the dielectric layer;
  - (e) anisotropically etching the mask layer to form a sidewall mask layer on sides of the gate electrode over the dielectric layer;

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